

SANYO

No.3508A

2SK1467

N-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

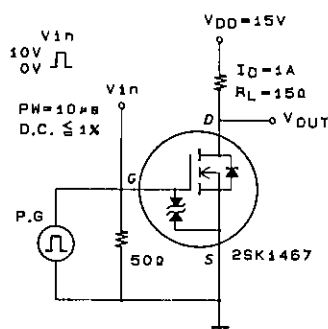
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DS}	30	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	2	A
Drain Current(Pulse)	I_{DP}	8	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ\text{C}$ Mounted on ceramic board ($250\text{mm}^2 \times 0.8\text{mm}$)	3.5 1.5 W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ\text{C}$

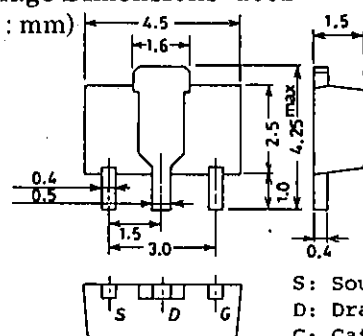
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	30			V
Zero Gate Voltage	I_{DSS}	$V_{DS} = 30\text{V}, V_{GS} = 0$			100	μA
Drain Current						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	1.0		2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 1\text{A}$	1.2	2.0		S
Static Drain to Source	$R_{DS(on)}$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$		0.2	0.3	Ω
on State Resistance	$R_{DS(on)}$	$I_D = 1\text{A}, V_{GS} = 4\text{V}$		0.3	0.45	Ω
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		170		pF
Output Capacitance	C_{oss}	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		100		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		30		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7		ns
Rise Time	t_r	"		11		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		35		ns
Fall Time	t_f	"		25		ns
Diode Forward Voltage	V_{SD}	$I_S = 2\text{A}, V_{GS} = 0$		1.0		V

Marking: KC

Switching Time Test Circuit**Package Dimensions 2062**

(unit: mm)



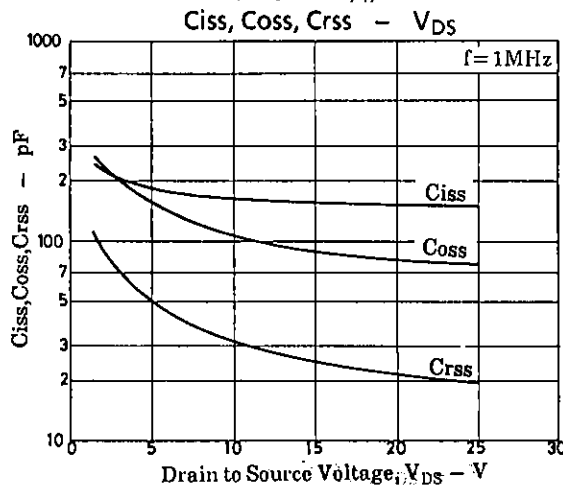
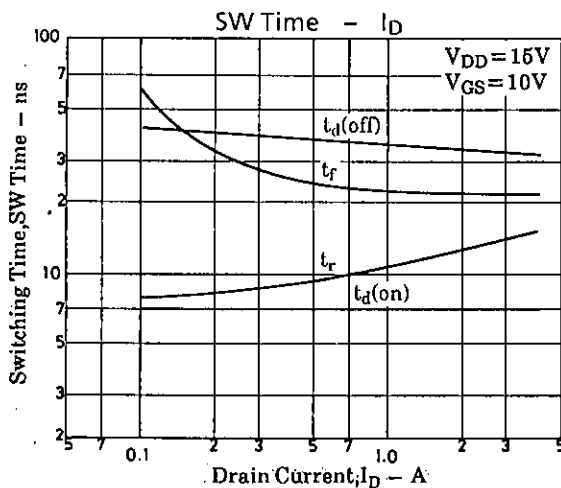
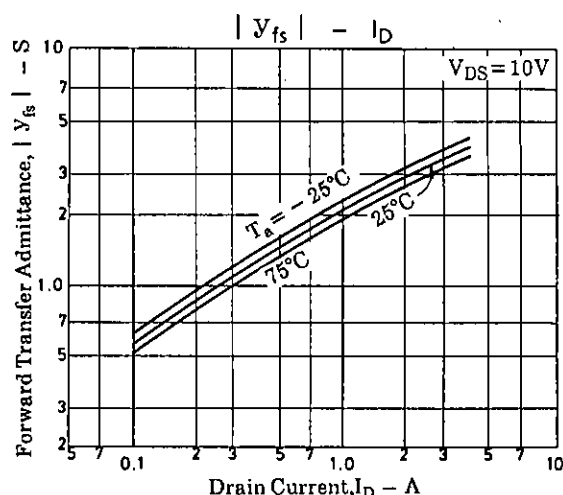
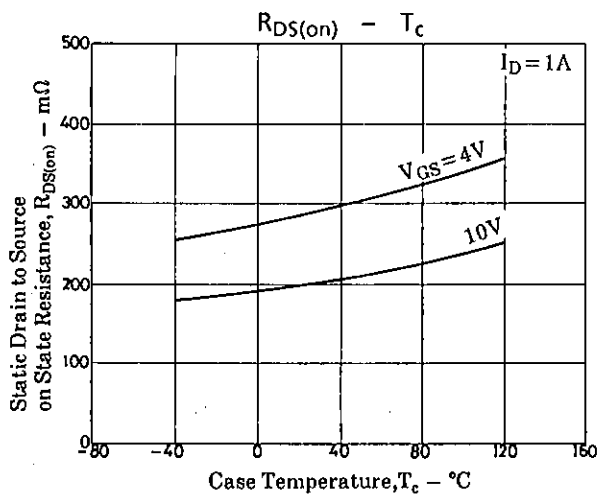
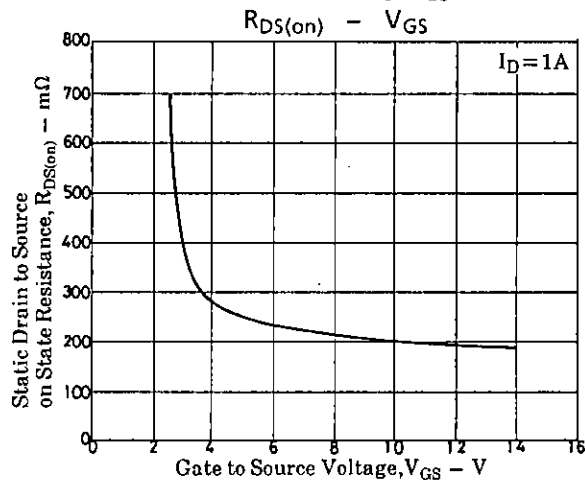
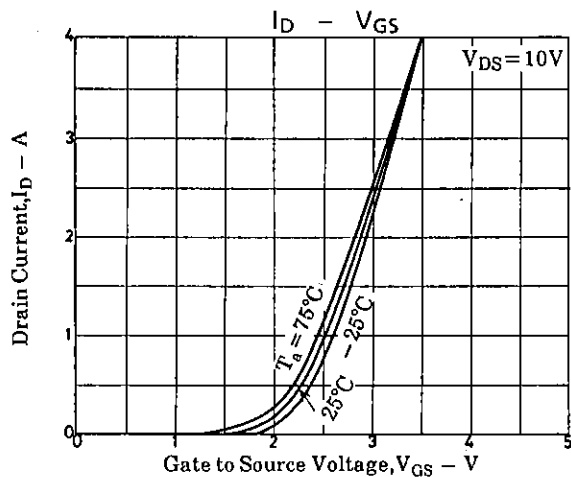
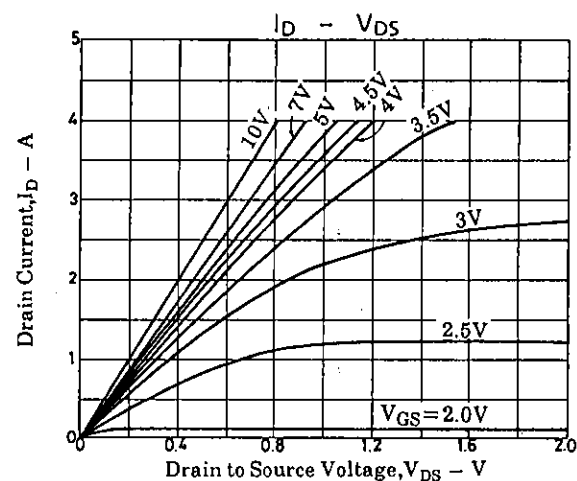
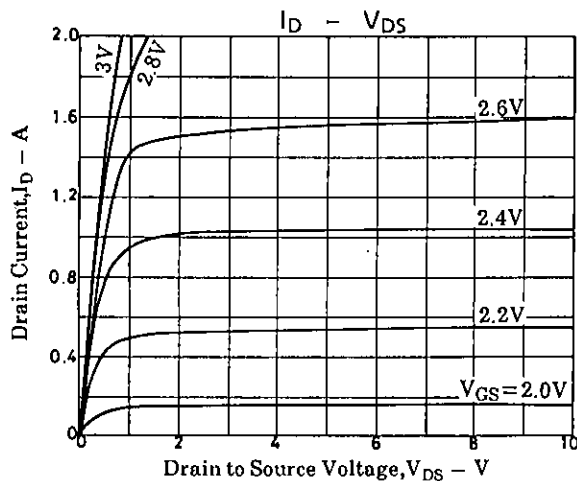
S: Source
D: Drain
G: Gate

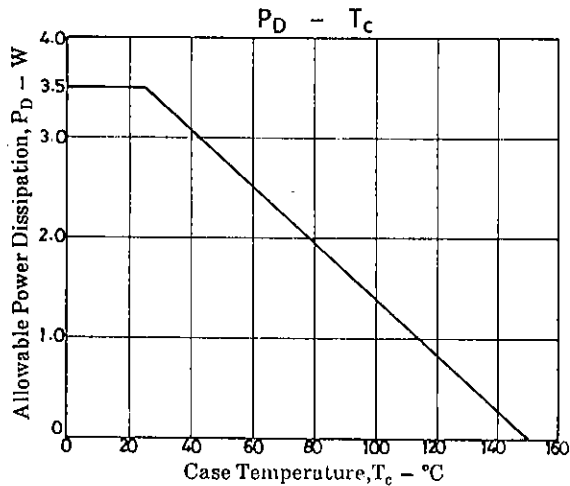
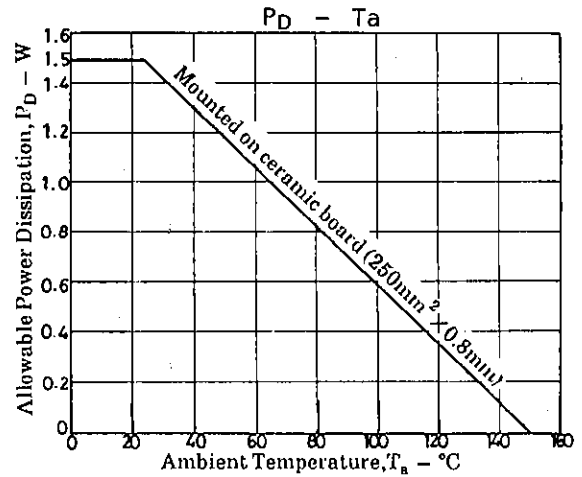
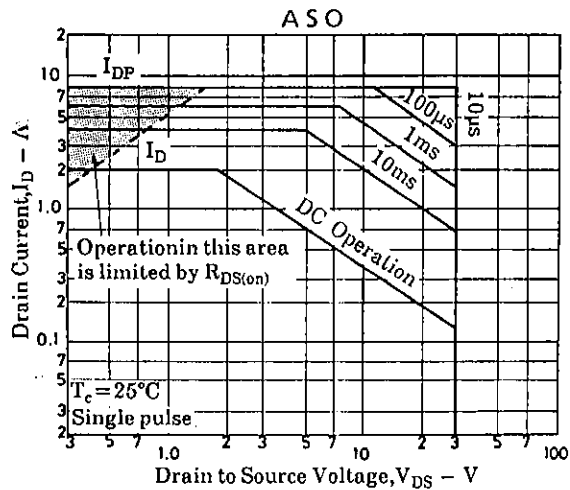
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